

ABSTRACT

ELECTRONIC DEVICE AND METHOD FOR FABRICATING THE SAME

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An electronic device including a semiconductor memory is provided. The semiconductor memory includes a plurality of first lines extending in a first direction; a plurality of second lines disposed over the first lines, the second lines extending in a second direction
10 crossing the first direction; a plurality of memory cells disposed between the first lines and the second lines at intersection regions of the first lines and the second lines; first liner layer patterns positioned on both sidewalls of each memory cell in the second direction; a first insulating layer pattern positioned between adjacent first liner layer
15 patterns in the second direction; second liner layer patterns positioned on both sidewalls of each memory cell in the first direction; a second insulating layer pattern positioned between adjacent second liner layer patterns in the first direction; and a third insulating layer positioned between adjacent second liner layer patterns in the second
20 direction.

FIG. 8A